

EH25 20

RoHS Compliant (Pb-free) 5.0V 4 Pad 5mm x 7mm Ceramic SMD HCMOS/TTL High Frequency Oscillator

Frequency Tolerance/Stability + ±20ppm Maximum

Operating Temperature Range -0°C to +70°C

### **ELECTRICAL SPECIFICATIONS**

Series -

Nominal Frequency	2.048MHz	
Frequency Tolerance/Stability	±20ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°C, Shock, and Vibration)	
Aging at 25°C	±5ppm/year Maximum	
Operating Temperature Range	0°C to +70°C	
Supply Voltage	5.0Vdc ±10%	
Input Current	50mA Maximum (No Load)	
Output Voltage Logic High (Voh)	2.4Vdc Minimum with TTL Load, Vdd-0.4Vdc Minimum with HCMOS Load (IOH= -16mA)	
Output Voltage Logic Low (Vol)	0.4Vdc Maximum with TTL Load, 0.5Vdc Maximum with HCMOS Load (IOH= +16mA)	
Rise/Fall Time	6nSec Maximum (Measured at 0.8Vdc to 2.0Vdc with TTL Load; Measured at 20% to 80% of waveform with HCMOS Load)	
Duty Cycle	50 $\pm$ 5(%) (Measured at 50% of waveform with TTL Load or with HCMOS Load)	
Load Drive Capability	10TTL Load or 50pF HCMOS Load Maximum	
Output Logic Type	CMOS	
Pin 1 Connection	Tri-State (High Impedance)	
Tri-State Input Voltage (Vih and Vil)	+2.2Vdc Minimum to enable output, +0.8Vdc Maximum to disable output (High Impedance), No Connect to enable output.	
Absolute Clock Jitter	±250pSec Maximum, ±100pSec Typical	
One Sigma Clock Period Jitter	±50pSec Maximum, ±30pSec Typical	
Start Up Time	10mSec Maximum	
Storage Temperature Range	-55°C to +125°C	

T TS -2.048M

L Pin 1 Connection

- Duty Cycle 50 ±5(%)

Tri-State (High Impedance)

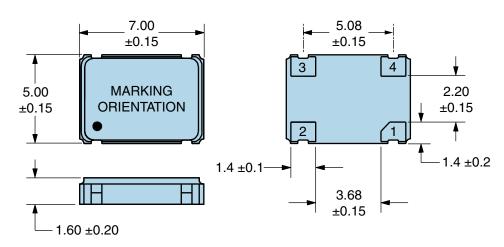
Nominal Frequency

2.048MHz

### **ENVIRONMENTAL & MECHANICAL SPECIFICATIONS**

MIL-STD-883, Method 3015, Class 1, HBM: 1500V	
MIL-STD-883, Method 1014, Condition A	
UL94-V0	
MIL-STD-883, Method 1014, Condition C	
MIL-STD-883, Method 2002, Condition B	
MIL-STD-883, Method 1004	
J-STD-020, MSL 1	
MIL-STD-202, Method 210, Condition K	
MIL-STD-202, Method 215	
MIL-STD-883, Method 2003	
MIL-STD-883, Method 1010, Condition B	
MIL-STD-883, Method 2007, Condition A	

## **MECHANICAL DIMENSIONS (all dimensions in millimeters)**



<b>ECLIPTEK</b> CORPORATION		
PIN	CONNECTION	
1	Tri-State	
2	Ground	
3	Output	
4	Supply Voltage	
	MARKING	

LINE	MARKING
1	ECLIPTEK
2	2.048M
3	XXXXXX XXXXX=Ecliptek Manufacturing Identifier

#### Suggested Solder Pad Layout

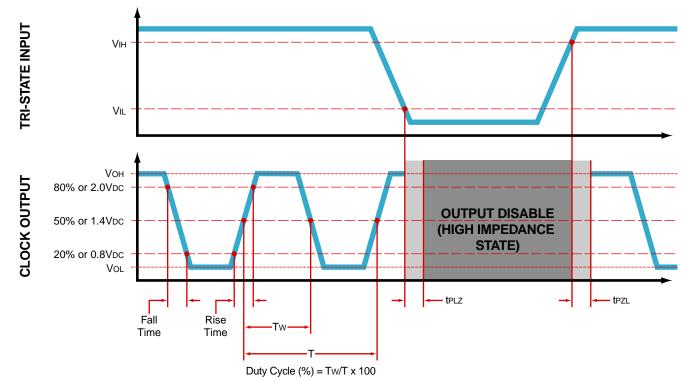
All Dimensions in Millimeters



All Tolerances are ±0.1



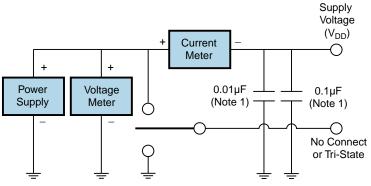
#### **OUTPUT WAVEFORM & TIMING DIAGRAM**

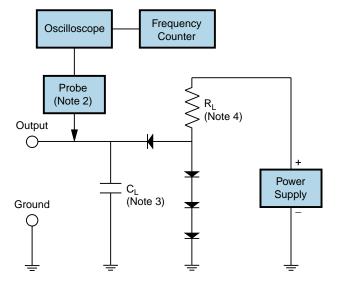


#### Test Circuit for TTL Output

Output Load Drive Capability	R <sub>L</sub> Value (Ohms)	C <sub>L</sub> Value (pF)
10TTL	390	15
5TTL	780	15
2TTL	1100	6
10LSTTL	2000	15
1TTL	2200	3







Note 1: An external 0.1µF low frequency tantalum bypass capacitor in parallel with a 0.01µF high frequency ceramic bypass capacitor close to the package ground and V<sub>DD</sub> pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth

(>300MHz) passive probe is recommended.

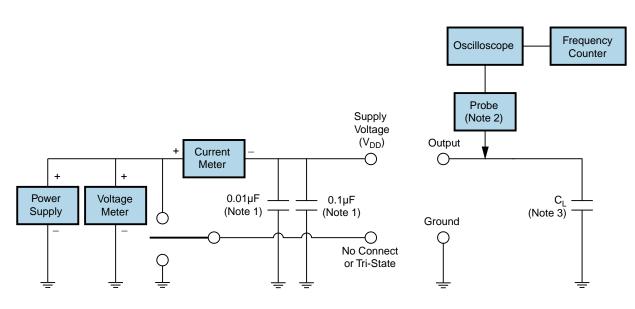
Note 3: Capacitance value  $C_L$  includes sum of all probe and fixture capacitance.

Note 4: Resistance value R<sub>L</sub> is shown in Table 1. See applicable specification sheet for 'Load Drive Capability'.

Note 5: All diodes are MMBD7000, MMBD914, or equivalent.



#### **Test Circuit for CMOS Output**



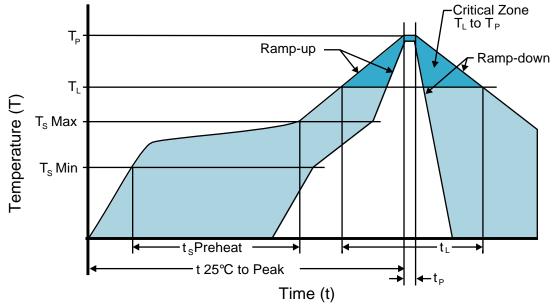
Note 1: An external 0.1µF low frequency tantalum bypass capacitor in parallel with a 0.01µF high frequency ceramic bypass capacitor close to the package ground and V<sub>DD</sub> pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value  $\dot{C}_1$  includes sum of all probe and fixture capacitance.

## **ECLIPTEK** CORPORATION

## **Recommended Solder Reflow Methods**



### High Temperature Infrared/Convection

EH2520TTS-2.048M

T <sub>s</sub> MAX to T <sub>L</sub> (Ramp-up Rate)	3°C/second Maximum
Preheat	
- Temperature Minimum (T <sub>s</sub> MIN)	150°C
- Temperature Typical (T <sub>s</sub> TYP)	175°C
<ul> <li>Temperature Maximum (T<sub>s</sub> MAX)</li> </ul>	200°C
- Time (t <sub>s</sub> MIN)	60 - 180 Seconds
Ramp-up Rate (T <sub>L</sub> to T <sub>P</sub> )	3°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	217°C
- Time (t∟)	60 - 150 Seconds
Peak Temperature (T <sub>P</sub> )	260°C Maximum for 10 Seconds Maximum
Target Peak Temperature (T <sub>P</sub> Target)	250°C +0/-5°C
Time within 5°C of actual peak (t <sub>p</sub> )	20 - 40 seconds
Ramp-down Rate	6°C/second Maximum
Time 25°C to Peak Temperature (t)	8 minutes Maximum
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.

## **ECLIPTEK** CORPORATION

## **Recommended Solder Reflow Methods**

EH2520TTS-2.048M



### Low Temperature Infrared/Convection 240°C

T <sub>s</sub> MAX to T <sub>L</sub> (Ramp-up Rate)	5°C/second Maximum
Preheat	
- Temperature Minimum (T <sub>s</sub> MIN)	N/A
<ul> <li>Temperature Typical (T<sub>s</sub> TYP)</li> </ul>	150°C
<ul> <li>Temperature Maximum (T<sub>s</sub> MAX)</li> </ul>	N/A
- Time (t <sub>s</sub> MIN)	60 - 120 Seconds
Ramp-up Rate (T⊾ to T <sub>P</sub> )	5°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	150°C
- Time (t∟)	200 Seconds Maximum
Peak Temperature (T <sub>P</sub> )	240°C Maximum
Target Peak Temperature (T <sub>P</sub> Target)	240°C Maximum 1 Time / 230°C Maximum 2 Times
Time within 5°C of actual peak (t <sub>P</sub> )	10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time
Ramp-down Rate	5°C/second Maximum
Time 25°C to Peak Temperature (t)	N/A
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.

#### Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

### **High Temperature Manual Soldering**

260°C Maximum for 5 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)